

REMARKS

Claims 1-11, 14-16, 33-40, 49, 50, 55, 56 and 61-76 are pending with claims 1, 6, 11, 33, 37, 61 and 69 being independent. Claim 12 has been canceled; claims 1, 6, 11, 33, 37 and 61 have been amended; and claims 66-76 have been added. The amendments to claims 1, 33 and 37 find support in the application at, for example, Fig. 1C. The amendments to claim 6 find support in the application at, for example, Fig. 3C. The amendments to claim 11 find support in the application at, for example, Fig. 2C. Finally, the amendments to claim 61, and the new claims, find support in the application at, for example, Fig. 4 and page 6, line 30 to page 7, line 9. No new matter has been introduced.

Claims 1-11, 14-16, 33-40, 49, 50, 55, 56 and 61-65 have been rejected as anticipated by Yamazaki (U.S. Patent No. 5,696,386).

With respect to claims 1 and 33, and their dependent claims, applicant requests reconsideration and withdrawal of this rejection because Yamazaki does not describe or suggest forming a diamond-like carbon film on a surface of a substrate that includes a thin film transistor on another surface, as recited in claims 1 and 33. Yamazaki discloses formation of an aluminum nitride film 102 on both faces of a substrate 101, and formation of a thin film transistor on one of the aluminum nitride films. As noted in the rejection, Yamazaki compares properties of aluminum nitride and diamond-like carbon films at col. 2, lines 47-67 and col. 3, lines 1-18. However, at col. 2, lines 55-62, Yamazaki criticizes diamond-like carbon films:

In general, a high thermal conductivity can be achieved by incorporating a diamond material such as a thin film of polycrystalline diamond, a hard carbon film, or a diamond-like carbon film. When a small area as the one in the device according to the present invention is considered, however, a satisfactory effect cannot be obtained because a tight adhesion cannot be obtained between a diamond material and a silicon oxide material.

Thus, Yamazaki indicates, in the context of a device such as is discussed by Yamazaki, that a diamond-like carbon film is not a suitable alternative for aluminum nitride. Accordingly, nothing in Yamazaki would have led one of ordinary skill in the art to modify the device of Yamazaki to replace the aluminum nitride layer with a diamond-like carbon film. Indeed, by criticizing

diamond-like carbon films, Yamazaki affirmatively teaches away from such a modification. Nor does Yamazaki directly describe including a diamond-like carbon film on a surface of a substrate that includes a thin film transistor on another surface. Accordingly, for at least these reasons, the rejection of claims 1 and 33, and their dependent claims, should be withdrawn.

With respect to claims 6 and 37, and their dependent claims, applicant requests reconsideration and withdrawal of this rejection because Yamazaki does not describe or suggest forming a diamond-like carbon film on a surface of a substrate, and forming a thin film transistor on an underlayer film formed on the diamond-like carbon film, as recited in claims 6 and 37. As discussed above, Yamazaki teaches away from replacing aluminum nitride with a diamond-like carbon film. In addition, while each of claims 6 and 37 recites "a wiring electrically connected to a thin film transistor" and "a pixel electrode formed over the wiring," Yamazaki discloses an arrangement in which a wiring is formed over a pixel electrode. Accordingly, for at least these reasons, the rejection should be withdrawn.

With respect to claim 11 and its dependent claims, applicant requests reconsideration and withdrawal of this rejection because Yamazaki does not describe or suggest forming a diamond-like carbon film between an interlayer insulating film and a pixel electrode, with the diamond-like carbon film including an opening through which the pixel electrode is connected. While the rejection indicates that element 110 of Yamazaki corresponds to the interlayer insulating film and elements 113/115 correspond to the pixel electrode, the rejection provides no indication of where a diamond-like carbon film between the two may be found. Accordingly, for at least this reason, the rejection should be withdrawn.

With respect to claim 61 and its dependent claims, applicant requests reconsideration and withdrawal of this rejection because, for the reasons discussed above with respect to claim 1, Yamazaki does not describe or suggest a device that includes a diamond-like carbon film, a substrate over the diamond-like carbon film, and a logic circuit comprising a transistor over the substrate.

Applicant also believes that new claim 69, and its dependent claims, are allowable because, for the reasons discussed above with respect to claim 6, Yamazaki does not describe or

Applicant : Takeshi Fukada
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suggest a device that includes a diamond-like carbon film and a logic circuit comprising a thin film transistor over the diamond-like carbon film.

Applicant submits that all claims are in condition for allowance.

The fees in the amount of \$1000 for the one-month extension of time fee (\$120), the extra claims fee (\$500), the one extra independent claim fee (\$200) and the information disclosure statement fee (\$180) are being paid concurrently herewith on the Electronic Filing System (EFS) by way of Deposit Account authorization. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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John F. Hayden
Reg. No. 37,640

Customer No. 26171
Fish & Richardson P.C.
1425 K Street, N.W., 11th Floor
Washington, DC 20005-3500
Telephone: (202) 783-5070
Facsimile: (202) 783-2331
/adt
40408190.doc